



# H2N6426

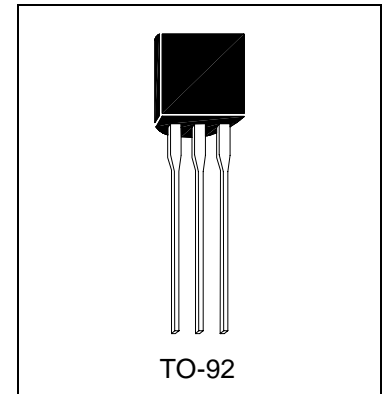
NPN EPITAXIAL PLANAR TRANSISTOR

## Description

Darlington Transistor

## Absolute Maximum Ratings

- Maximum Temperatures
  - Storage Temperature ..... -55 ~ +150 °C
  - Junction Temperature ..... +150 °C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation (T<sub>A</sub>=25°C) ..... 625 mW
- Maximum Voltages and Currents (T<sub>A</sub>=25°C)
  - BV<sub>CEO</sub> Collector to Emitter Voltage ..... 40 V
  - BV<sub>CBO</sub> Collector to Base Voltage ..... 40 V
  - BV<sub>EBO</sub> Emitter to Base Voltage ..... 12 V
  - I<sub>C</sub> Collector Current ..... 500 mA



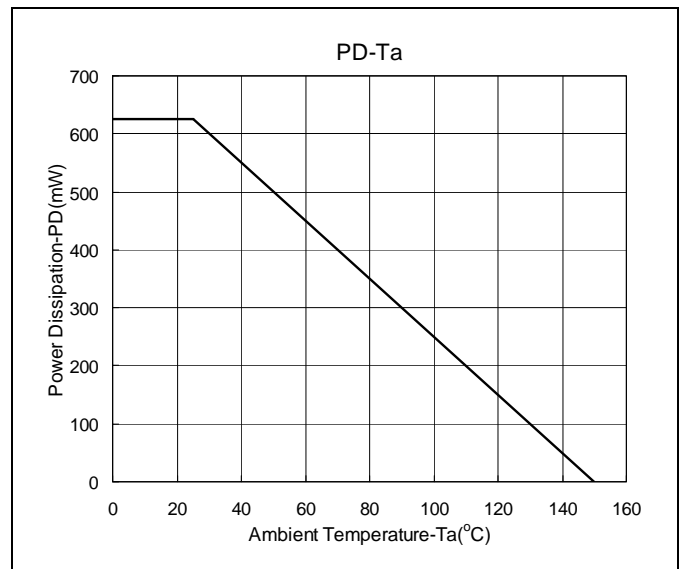
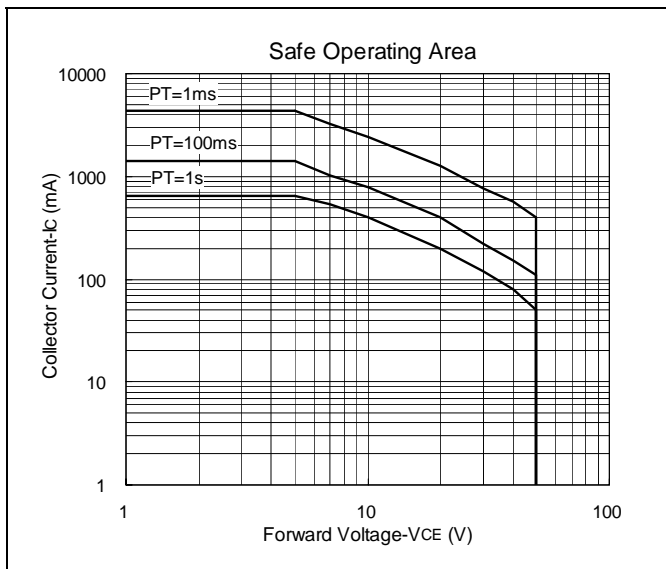
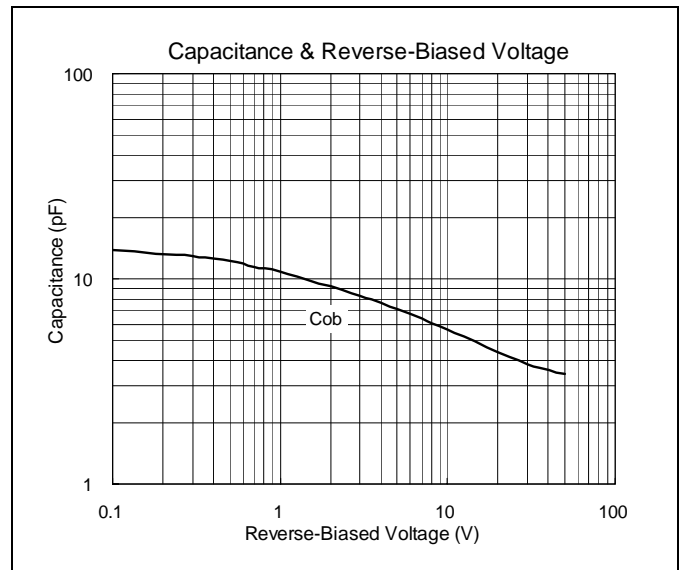
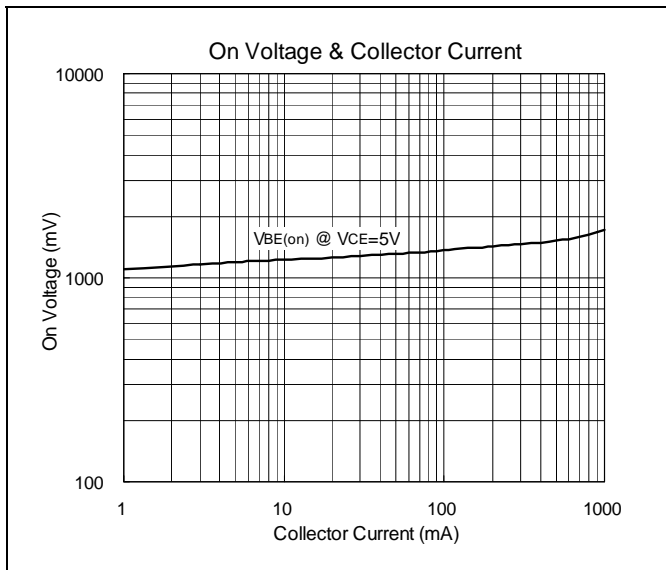
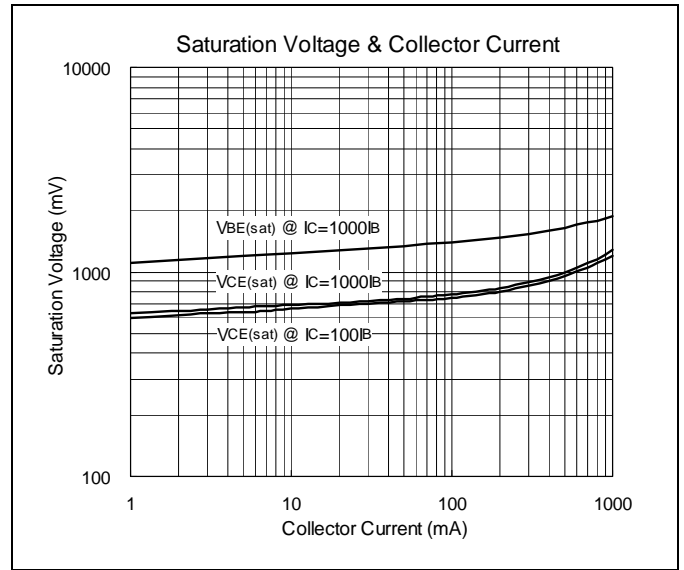
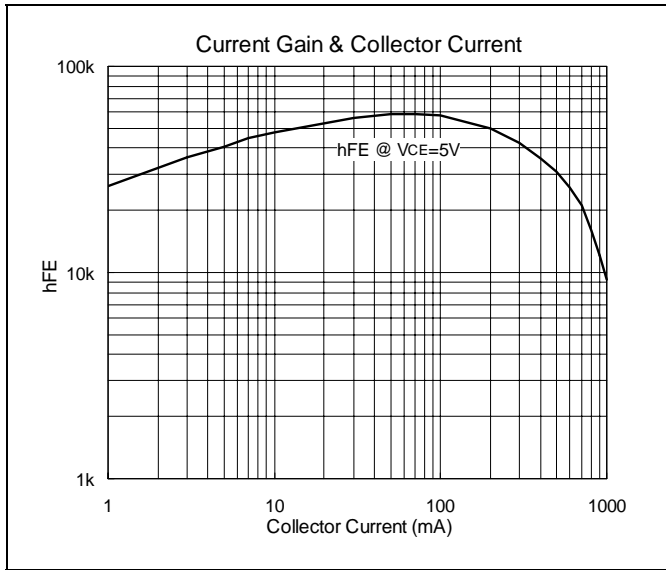
## Electrical Characteristics (T<sub>A</sub>=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CEO</sub>	40	-	-	V	I <sub>C</sub> =10mA, I <sub>B</sub> =0
BV <sub>CBO</sub>	40	-	-	V	I <sub>C</sub> =100uA, I <sub>E</sub> =0
BV <sub>EBO</sub>	12	-	-	V	I <sub>E</sub> =10uA, I <sub>C</sub> =0
I <sub>CEO</sub>	-	-	1.0	uA	V <sub>EB</sub> =25V, I <sub>B</sub> =0
I <sub>CBO</sub>	-	-	50	nA	V <sub>CB</sub> =30V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	50	nA	V <sub>EB</sub> =10V, I <sub>C</sub> =0
*V <sub>CE(sat)1</sub>	-	0.71	1.2	V	I <sub>C</sub> =50mA, I <sub>B</sub> =0.5mA
*V <sub>CE(sat)2</sub>	-	0.9	1.5	V	I <sub>C</sub> =500mA, I <sub>B</sub> =0.5mA
*V <sub>BE(sat)</sub>	-	1.52	2.0	V	I <sub>C</sub> =500mA, I <sub>B</sub> =0.5mA
V <sub>BE(on)</sub>	-	1.24	1.75	V	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA
*h <sub>FE1</sub>	20	-	200	K	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA
*h <sub>FE2</sub>	30	-	300	K	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA
*h <sub>FE3</sub>	20	-	200	K	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA
Cob	-	5.4	7.0	pF	V <sub>CB</sub> =10V, f=1MHz

\*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%



### Characteristics Curve





### TO-92 Dimension

3-Lead TO-92 Plastic Package  
HSMC Package Code: A

**Marking:**

Pb Free Mark  
 Pb-Free: "●" (Note)  
 Normal: None

H 2 N  
6 4 2 6

Date Code      Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Emitter 2.Base 3.Collector

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

\*: Typical, Unit: mm

### TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1,F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

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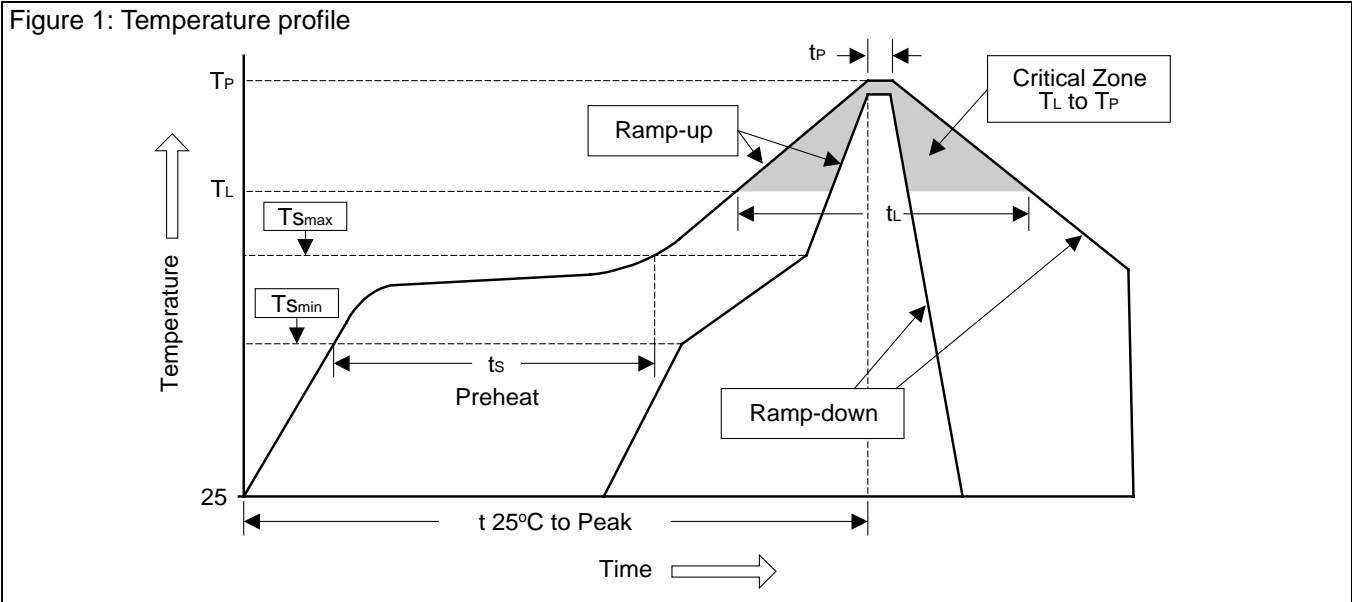
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### Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ( $T_{Smin}$ )	100°C	150°C
- Temperature Max ( $T_{Smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60~120 sec	60~180 sec
$T_{Smax}$ to $T_L$		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60~150 sec	60~150 sec
Peak Temperature ( $T_P$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec